

HIGH-SPEED 16K X 9 DUAL-PORT STATIC RAM

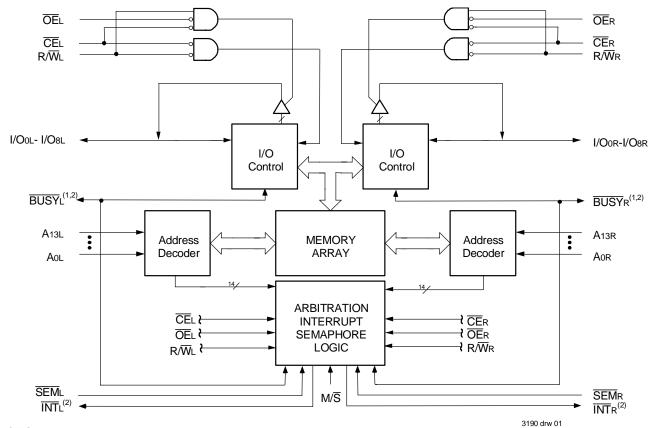
Features

 True Dual-Ported memory cells which allow simultaneous reads of the same memory location

High-speed access

- Commercial:12/15/20/25/35ns (max.)
- Industrial: 20ns (max.)
- Military: 20/25/35ns (max.)
- Low-power operation
- IDT7016S
 - Active: 750mW (typ.) Standby: 5mW (typ.)
 - IDT7016L
 Active: 750mW (typ.)
 Standby: 1mW (typ.)

- IDT7016 easily expands data bus width to 18 bits or more using the Master/Slave select when cascading more than one device
- M/S = VIH for BUSY output flag on Master M/S = VIL for BUSY input on Slave
- Busy and Interrupt Flag
- On-chip port arbitration logic
- Full on-chip hardware support of semaphore signaling between ports
- * Fully asynchronous operation from either port
- TTL-compatible, single 5V (±10%) power supply
- Available in ceramic 68-pin PGA, 68-pin PLCC, and an 80pin TQFP
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- * Green parts available, see ordering information



Functional Block Diagram

NOTES:

- In MASTER mode: BUSY is an output and is a push-pull driver In SLAVE mode: BUSY is input.
- 2. BUSY outputs and INT outputs are non-tri-stated push-pull drivers.

JANUARY 2009

Military, Industrial and Commercial Temperature Ranges

Description

The IDT7016 is a high-speed 16K x 9 Dual-Port Static RAM. The IDT7016 is designed to be used as stand-alone Dual-Port RAMs or as a combination MASTER/SLAVE Dual-Port RAM for 18-bit-or-more wider systems. Using the IDT MASTER/SLAVE Dual-Port RAM approach in 18bit or wider memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

This device provides two independent ports with separate control. address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature controlled by CE permits the on-chip circuitry of each port to enter a very low standby power mode.

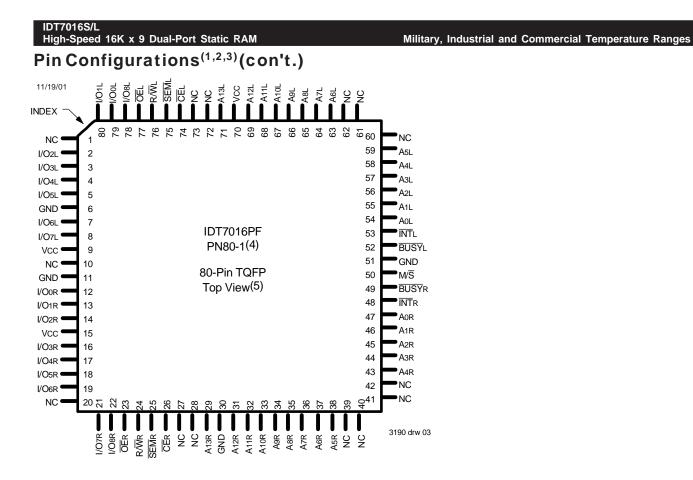
Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 750mW of power.

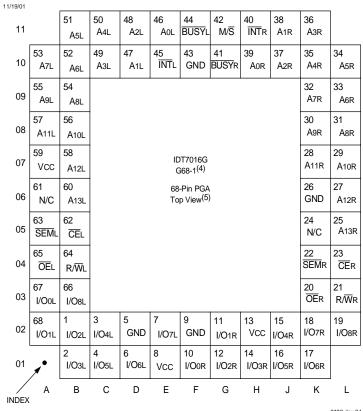
The IDT7016 is packaged in a ceramic 68-pin PGA, a 64-pin PLCC and an 80-pinTQFP (Thin Quad Flatpack). Military grade product is manufactured in compliance with the latest revision of MIL-PRF-38535 QML, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.

Pin Configurations^(1,2,3) 11/19/01 1/08L 0日 1/08L 1/08L 1/08L 1/07 1/ 100 Q INDEX 7 6 5 4 3 2 1 68 67 66 65 64 63 62 61 9 8 I/O2L 10 🗆 A5l 60 I/O3L []11 🗆 A4L 59 I/O4L 12 🗆 Азь 58 I/O5L 13 57 🗆 A2L GND 14 56 ⊐ A1L I/O6L 15 55 AOL IDT7016J I/O7L 16 J68-1(4) 54 Vcc 117 53 GND 18 68-Pin PLCC 52 🗆 GND I/OOR 19 Top View(5) 51 M/S I/O1R 20 50 BUSYR I/O2R 21 49 **INT**R Vcc 22 48 A0R I/O3R 23 47 A1R I/O4R 24 46 A2R I/O5R 25 🗆 Азг 45 I/O6R 26 44 A4R 30 31 38 Ajr Agr Asr 3190 drw 02 Pin Names (7016)

- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground supply.
- Package body is approximately .95 in x .95 in x .17 in. 3.
- 4. This package code is used to reference the package diagram.
- 5. This text does not imply orientation of Part-marking.

Left Port	Right Port	Names
CEL	ĒĒR	Chip Enable
R/WL	R/WR	Read/Write Enable
ŌĒL	ŌĒR	Output Enable
Aol - A13l	Aor - A13r	Address
I/Ool - I/O8l	I/Oor - I/O8r	Data Input/Output
SEML	SEMR	Semaphore Enable
ĪNTL	ĪNTr	Interrupt Flag
BUSYL	BUSYR	Busy Flag
М	/\$	Master or Slave Select
V	CC	Power
Gl	ND	Ground





NOTES:

- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground supply.
- 3. PN80-1 package body is approximately 14mm x 14mm x 1.4mm. G68-1 package body is approximately 1.18 in x 1.18 in x .16 in.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

3190 drw 04

Truth Table I: Non-Contention Read/Write Control

	Inpu	uts ⁽¹⁾		Outputs				
ĈĒ	R/W	ŌĒ	SEM	I/O0-8	Mode			
Н	Х	Х	Н	High-Z	Deselcted: Power-Down			
L	L	Х	Н		Write to Memory			
L	Н	L	Н	DATAOUT	Read Memory			
Х	Х	Н	Х	High-Z	Outputs Disabled			

NOTE:

IDT7016S/L

1. Condition: AoL — A13L \neq AOR — A13R

Truth Table II: Semaphore Read/Write Control⁽¹⁾

	Inp	outs		Outputs				
ĈĒ	R∕₩	ŌĒ	SEM	I/O0-8	Mode			
Н	Н	L	L	DATAOUT	Read Semaphore Flag Data Out (I/Oo - I/Os)			
Н	\uparrow	Х	L	DATAIN	Write I/Oo into Semaphore Flag			
L	Х	Х	L		Not Allowed			

NOTE:

1. There are eight semaphore flags written to via I/Oo and read from all I/Os (I/Oo-I/Os). These eight semaphores are addressed by Ao - A2.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Military	Unit
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
Tbias	Temperature Under Bias	-55 to +125	-65 to +135	°C
Tstg	Storage Temperature	-65 to +150	-65 to +150	°C
Ιουτ	DC Output Current	50	50	mA
				3190 tbl 04

NOTES:

- 1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq Vcc + 10%.

Maximum Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	Vcc
Military	-55°C to +125°C	0V	5.0V <u>+</u> 10%
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%
NOTEO			3190 tbl 05

NOTES:

1. This is the parameter TA. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit			
Vcc	Supply Voltage	4.5	5.0	5.5	۷			
GND	Ground	0	0	0	V			
Vih	Input High Voltage	2.2		6.0 ⁽²⁾	V			
VIL	Input Low Voltage	-0.5(1)	_	0.8	V			
	3190 tbl 06							

NOTES:

1. VIL \geq -1.5V for pulse width less than 10ns.

2. VTERM must not exceed Vcc + 10%.

3190 tbl 03

3190 tbl 02

Military, Industrial and Commercial Temperature Ranges

Capacitance⁽¹⁾

(TA = +25℃, f = 1.0mhz, for TQFP ONLY)

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit				
Cin	Input Capacitance	Vıℕ = 3dV	9	pF				
Соит	Output Capacitance	Vout = 3dV	10	pF				
3190 tbl 07								

NOTES:

1. This parameter is determined by device characteristics but is not production tested.

2. 3dV references the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V .

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (Vcc = 5.0V ± 10%)

			7016S		701		
Symbol	Parameter	Test Conditions		Max.	Min.	Max.	Unit
llul	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, ViN = 0V to Vcc	_	10	_	5	μA
lllol	Output Leakage Current	$\overline{CE} = V_{\mathbb{H}}, V_{OUT} = 0V \text{ to } V_{CC}$	—	10	_	5	μA
Vol	Output Low Voltage	IoL = +4mA	_	0.4	_	0.4	V
Vон	Output High Voltage	Ioh = -4mA	2.4	-	2.4	-	۷

NOTE:

1. At Vcc \leq 2.0V, Input leakages are undefined.

Output Loads and AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1 and 2
	3100 #1 00

3190 tbl 09

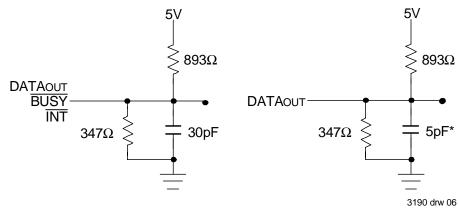


Figure 1. AC Output Test Load

Figure 2. Output Test Load (for tLz, tHz, twz, tow) *Including scope and jig. 3190 tbl 08

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽¹⁾ (con't.) ($Vcc = 5.0V \pm 10\%$)

			Test Condition Version			6X12 Only		6X15 IOnly	
Symbol	Parameter	Test Condition			Typ. ⁽²⁾	Max.	Typ. ⁽²⁾	Max.	Unit
ICC	Dynamic Operating Current (Both Ports Active)	CE = VIL, Outputs Disabled SEM = VIH f = tMax ^{®)}	COM'L	S L	170 170	325 275	170 170	310 260	mA
	(DOIN POILS ACTIVE)	'MAX*'	MIL & IND	S L					
ISB1	Standby Current (Both Ports - TTL Level Inputs)	$\frac{\overline{CE}R = \overline{CE}L = VH}{\overline{SEM}R = \overline{SEM}L = VH}$	COM'L	S L	25 25	70 60	25 25	60 50	mA
	Level inpus)	$f = f_{MAX}^{(3)}$	MIL & IND	S L					
IS B2	Standby Current (One Port - TTL Active Port Outputs Disabled,		COM'L	S L	105 105	200 170	105 105	190 160	mA
	Level Inputs)	$\overline{SEMR} = \overline{SEML} = VH$	MIL & IND	S L					
IS B3	Full Standby Current (Both Ports - All CMOS Level Inputs)	Both Ports \overline{CE}_{L} and $\overline{CE}_{R} \ge Vcc - 0.2V$	COM'L	S L	1.0 0.2	15 5	1.0 0.2	15 5	mA
	Level inpus)	$ \begin{array}{l} \mathbb{V}\mathbb{N} \geq \mathbb{V}\mathbb{C}\mathbb{C} \ \text{-} \ 0.2\mathbb{V} \ \text{or} \\ \frac{\mathbb{V}\mathbb{N} \leq 0.2\mathbb{V}, \ f = 0^{(4)}}{\mathbb{S}\mathbb{E}\mathbb{M}\mathbb{R}} = \mathbb{S}\mathbb{E}\mathbb{M}\mathbb{L} \geq \mathbb{V}\mathbb{C}\mathbb{C} \ \text{-} \ 0.2\mathbb{V} \end{array} $	MIL & IND	S L					
ISB4	(One Port - All CMOS $\overline{CF}_{B'} > V_{CC} - 0.2V^{(5)}$	COM'L	S L	100 100	180 150	100 100	170 140	mA	
	Level Inputs)	$ \begin{array}{l} \overline{\text{SEMR}} = \overline{\text{SEML}} \geq Vcc - 0.2V \\ V\text{IN} \geq Vcc - 0.2V \\ or V\text{IN} \leq 0.2V \\ \text{Active Port Outputs Disabled} \\ f = \text{fmax}^{(0)} \end{array} $	MIL & IND	S L					

					Com	6X20 'I, Ind ilitary	Con	6X25 n'I& tary	Con	6X35 n'I & itary	
Symbol	Parameter	Test Condition	Versio	on	Typ. ⁽²⁾	Max.	Typ. ⁽²⁾	Max.	Typ. ⁽²⁾	Max.	Unit
ICC	Dynamic Operating Current (Both Ports Active)	\overline{CE} = VIL, Outputs Disabled SEM = VH f = $Max^{(0)}$	COM'L	S L	160 160	290 240	155 155	265 220	150 150	250 210	mA
		T = IMAX ⁽⁰⁾	MIL & IND	S L	160 160	380 310	155 155	340 280	150 150	300 250	
ISB1	Standby Current (Both Ports - TTL	$\frac{\overline{CER} = \overline{CEL} = VH}{SEMR = SEML = VH}$	COM'L	S L	20 20	60 50	16 16	60 50	13 13	60 50	mA
	Level Inputs)	$f = f_{MAX}^{(3)}$	MIL & IND	S L	20 20	80 65	16 16	80 65	13 13	80 65	
IS B2	Standby Current (One Port - TTL	$\overline{CE}^{*}A^{*} = VIL and \overline{CE}^{*}B^{*} = VIH^{(5)}$ Active Port Outputs Disabled,	COM'L	S L	95 95	180 150	90 90	170 140	85 85	155 130	mA
	Level Inputs)	$\frac{f = f_{MAX}^{(3)}}{SEMR} = \overline{SEML} = VIH$	MIL & IND	S L	95 95	240 210	90 90	215 180	85 85	190 160	
IS B3	Full Standby Current (Both Ports - All CMOS	Both Ports \overline{CE} and $\overline{CE}_{R} \ge Vcc + 0.2V$	COM'L	S L	1.0 0.2	15 5	1.0 0.2	15 5	1.0 0.2	15 5	mA
	Level Inputs) VIN ≥ Vcc - 0.2V or VIN ≤ 0.2V, f = 0 ⁽⁴⁾ SEMR = SEML ≥ Vcc - 0.2V	$V_{IN} < 0.2V$, f = 0 ⁽⁴⁾	MIL & IND	S L	1.0 0.2	30 10	1.0 0.2	30 10	1.0 0.2	30 10	
ISB4	Full Standby Current (One Port - All CMOS Level Inputs)	$\frac{\overline{CE}^{*}A^{*}}{\overline{CE}^{*}B^{*}} \ge \frac{0.2V \text{ and }}{2CC} = 0.2V^{(5)}$	COM'L	S L	90 90	155 130	85 85	145 120	80 80	135 110	mA
	inpus)	$ \begin{array}{l} \overline{\text{SEMR}} = \overline{\text{SEML}} \geq \text{Vcc} - 0.2\text{V} \\ \overline{\text{Vin}} \geq \text{Vcc} - 0.2\text{V} \text{ or } \overline{\text{Vin}} \leq 0.2\text{V} \\ \text{Active Port Outputs Disabled} \\ f = f_{MAX}^{(6)} \end{array} $	MIL & IND	S L	90 90	230 200	85 85	200 170	80 80	175 150	

NOTES:

1. 'X' in part numbers indicates power rating (S or L)

2. Vcc = 5V, TA = $+25^{\circ}$ C, and are not production tested. lcccc = 120mA(typ.) 3. At f = fMAX, address and I/Os are cycling at the maximum frequency read cycle of 1/tRc.

4. f = 0 means no address or control lines change.

5. Port "A" may be either left or right port. Port "B" is the opposite of Port "A".

3190 tbl 11

3190 tbl 10

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁴⁾

					7016X15 Com'l Only	
Symbol			Max.	Unit		
READ CYCLE						
tRC	Read Cycle Time	12		15	—	ns
tAA	Address Access Time		12		15	ns
TACE	Chip Enable Access Time ⁽³⁾		12		15	ns
taoe	Output Enable Access Time	—	8	_	10	ns
tон	Output Hold from Address Change	3	_	3	_	ns
١LZ	Output Low-Z Time ^(1,2)	3		3	_	ns
tHZ	Output High-Z Time ^(1,2)	—	10	_	10	ns
t₽U	Chip Enable to Power Up Time ⁽²⁾	0		0	_	ns
tPD	Chip Disable to Power Down Time ⁽²⁾		12		15	ns
tSOP	Semaphore Flag Update Pulse (OE or SEM)	10		10	—	ns
t SAA	Semaphore Address Access Time		12		15	ns

3190 tbl 12a

		7016X20 Com'l, Ind & Military		7016X25 Com'l & Military		7016X35 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYCLE								
tRC	Read Cycle Time	20		25		35		ns
taa	Address Access Time		20	_	25		35	ns
tACE	Chip Enable Access Time ⁽³⁾		20		25	-	35	ns
t AOE	Output Enable Access Time		12		13		20	ns
tOH	Output Hold from Address Change	3	_	3		3		ns
tLz	Output Low-Z Time ^(1,2)	3		3	_	3		ns
tнz	Output High-Z Time ^(1,2)		12		15		20	ns
t₽U	Chip Enable to Power Up Time ⁽²⁾	0		0		0		ns
tPD	Chip Disable to Power Down Time ⁽²⁾		20		25	_	35	ns
tSOP	Semaphore Flag Update Pulse (OE or SEM)	10		10		10	_	ns
tSAA	Semaphore Address Access Time		20		25		35	ns

3190 tbl 12b

NOTES:

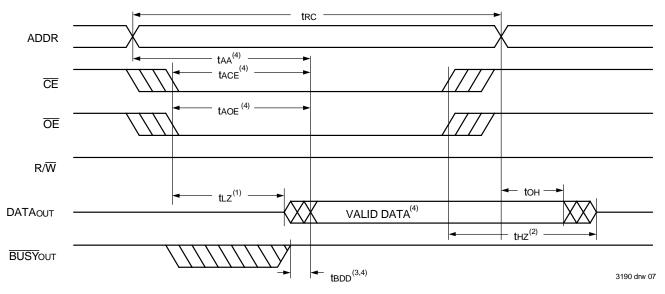
1. Transition is measured 0mV from Low- or High-impedance voltage with Output Test Load (Figure 2).

2. This parameter is guaranteed by device characterization but not production tested.

3. To access RAM, CE = VIL and SEM = VIH. To access semaphore, CE = VIH and SEM = VIL.

4. 'X' in part numbers indicates power rating (S or L).

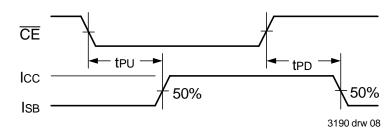
Waveform of Read Cycles⁽⁵⁾



NOTES:

- 1. Timing depends on which signal is asserted last, $\overline{\text{OE}}$ or $\overline{\text{CE}}$.
- 2. Timing depends on which signal is de-asserted first, CE or OE.
- 3. tedd delay is required only in cases where the opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relation to valid output data.
- 4. Start of valid data depends on which timing becomes effective last: tAOE, tACE, tAA or tBDD.
- 5. $\overline{\text{SEM}} = \text{VIH}.$

Timing of Power-Up / Power-Down



3190 tbl 13b

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage⁽⁵⁾

			7016X12 Com'l Only		7016X15 Com'l Only	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
WRITE CYCLI	E					
twc	Write Cycle Time	12		15	_	ns
tew	Chip Enable to End-of-Write ⁽³⁾	10		12	_	ns
taw	Address Valid to End-of-Write	10		12	—	ns
tas	Address Set-up Time ⁽³⁾	0		0	_	ns
twp	Write Pulse Width	10		12	_	ns
twn	Write Recovery Time	2		2	_	ns
tow	Data Valid to End-of-Write	10		10	_	ns
tHZ	Output High-Z Time ^(1,2)		10	—	10	ns
tDH	Data Hold Time ⁽⁴⁾	0		0	_	ns
twz	Write Enable to Output in High-Z ^(1,2)		10	—	10	ns
tow	Output Active from End-of-Write ^(1,2,4)	3		3	_	ns
tSWRD	SEM Flag Write to Read Time	5		5	—	ns
tSP S	SEM Flag Contention Window	5		5	_	ns
	-	•	•	•	-	3190 tbl 13

		Com'l, Ind Cor		Con	6X25 n'I & itary	l & Com'l &		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE CYCLE			-	-			-	-
twc	Write Cycle Time	20		25		35	_	ns
tew	Chip Enable to End-of-Write ⁽³⁾	15		20		30	_	ns
taw	Address Valid to End-of-Write	15		20		30	_	ns
tas	Address Set-up Time ⁽³⁾	0		0		0		ns
twp	Write Pulse Width	15		20	_	25	_	ns
twR	Write Recovery Time	2		2	_	2	_	ns
tow	Data Valid to End-of-Write	15		15	_	15		ns
tHZ	Output High-Z Time ^(1,2)		12	-	15		20	ns
tDH	Data Hold Time ⁽⁴⁾	0		0		0	_	ns
twz	Write Enable to Output in High-Z ^(1,2)		12		15		20	ns
tow	Output Active from End-of-Write ^(1,2,4)	3		3	_	3		ns
tSWRD	SEM Flag Write to Read Time	5		5		5		ns
tSP S	SEM Flag Contention Window	5		5	_	5		ns

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).

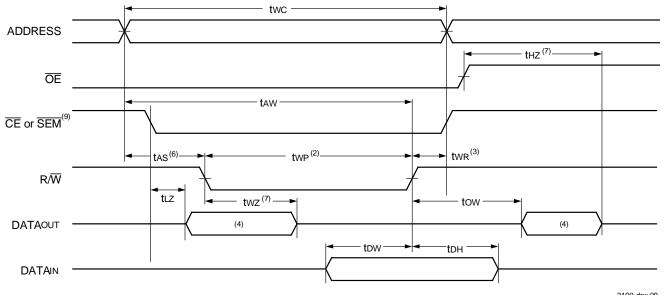
2. This parameter is guaranteed by device characterization but not production tested.

3. To access RAM, \overrightarrow{CE} = VIL and \overrightarrow{SEM} = VIH. To access semaphore, \overrightarrow{CE} = VIH and \overrightarrow{SEM} = VIL. Either condition must be valid for the entire tew time.

4. The specification for tDH must be met by the device supplying write data to the RAM under all operating conditions. Although tDH and tow values will vary over voltage and temperature, the actual tDH will always be smaller than the actual tow.

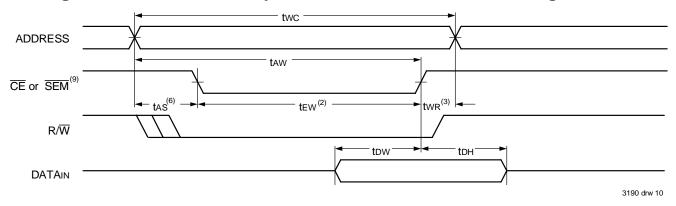
5. 'X' in part numbers indicates power rating (S or L).

Timing Waveform of Write Cycle No. 1, R/W Controlled Timing^(1,5,8)



3190 drw 09

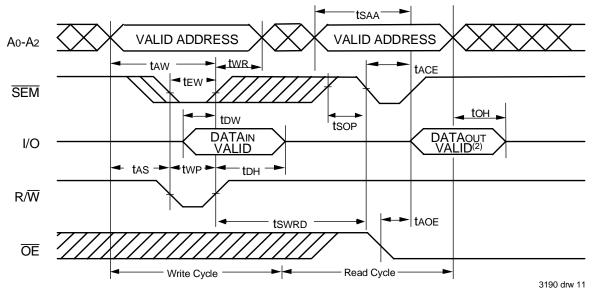
Timing Waveform of Write Cycle No. 2, **CE** Controlled Timing^(1,5)



- 1. $R\overline{W}$ or \overline{CE} must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a LOW CE and a LOW R/W for memory array writing cycle.
- 3. twn is measured from the earlier of CE or R/W (or SEM or R/W) going HIGH to the end of write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE or SEM LOW transition occurs simultaneously with or after the RW LOW transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal is asserted last, \overline{CE} or R/\overline{W} .
- 7. This parameter is guaranteed by device characterization but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If OE is LOW during RW controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off and data to be placed on the bus for the required tow. If OE is HIGH during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 9. To access RAM, CE = VIL and SEM = VIH. To access Semaphore, CE = VIH and SEM = VIL tew must be met for either condition.

Military, Industrial and Commercial Temperature Ranges

Timing Waveform of Semaphore Read after Write Timing, Either Side⁽¹⁾

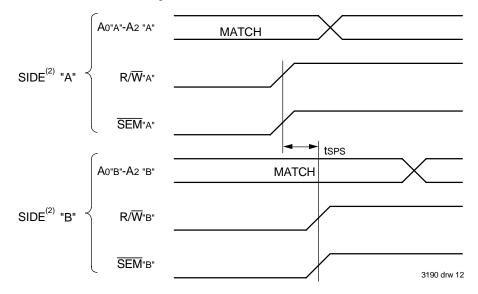


NOTES:

1. $\overline{CE} = VIH$ for the duration of the above timing (both write and read cycle).

2. "DATAOUT VALID" represents all I/O's (I/Oo-I/O8) equal to the semaphore value.

Timing Waveform of Semaphore Write Condition^(1,3,4)



- 1. DOR = DOL =VIH, $\overline{CE}R = \overline{CE}L = VIH$.
- 2. All timing is the same for left and right ports. Port"A" may be either left or right port. "B" is the opposite port from "A".
- 3. This parameter is measured from RW "A" or SEM "A" going HIGH to R/W "B" or SEM "B" going HIGH.
- 4. If tsps is not satisfied, there is no guarantee which side will obtain the semaphore flag.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁶⁾

		7016X12 Com'l Only			7016X15 Com'l Only	
Symbol	Parameter	Min.	Мах.	Min.	Max.	Unit
BUSY TIMING	G (M/S = VIH)		-			-
t BAA	BUSY Access Time from Address Match		12	—	15	ns
t BDA	BUSY Disable Time from Address Not Matched		12	_	15	ns
t BAC	BUSY Access Time from Chip Enable Low	—	12		15	ns
tBDC	BUSY Disable Time from Chip Enable High	—	12		15	ns
taps	Arbitration Priority Set-up Time ⁽²⁾	5		5	—	ns
tBDD	BUSY Disable to Valid Data ⁽³⁾	—	15		18	ns
twн	Write Hold After BUSY ⁽⁵⁾	11		13	—	ns
BUSY INPUT	TIMING (M/S = VIL)					-
twв	BUSY Input to Write ⁽⁴⁾	0		0	—	ns
twн	Write Hold After BUSY ⁽⁵⁾	11		13	_	ns
PORT-TO-PO	RT DELAY TIMING					-
twdd	Write Pulse to Data Delay ⁽¹⁾		25		30	ns
todd	Write Data Valid to Read Data Delay ⁽¹⁾		20		25	ns
		-		-	-	3190 tbl 14

		Com	Com'l, Ind		6X25 n'I& itary	7016X35 Com'l & Military			
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit	
BUSY TIMING	(M/S̄ = Vін)								
B AA	BUSY Access Time from Address Match	_	20		20		20	ns	
t BDA	BUSY Disable Time from Address Not Matched	_	20		20		20	ns	
t BAC	BUSY Access Time from Chip Enable Low	_	20		20		20	ns	
tBDC	BUSY Disable Time from Chip Enable High	_	17		17		20	ns	
taps	Arbitration Priority Set-up Time ⁽²⁾	5		5		5		ns	
tBDD	BUSY Disable to Valid Data ⁽³⁾	_	30		30		35	ns	
twн	Write Hold After BUSY ⁽⁵⁾	15		17		25		ns	
BUSY INPUT	TIMING (M/ \overline{S} = VIL)								
twв	BUSY Input to Write ⁽⁴⁾	0	_	0	_	0		ns	
twн	Write Hold After BUSY ⁽⁵⁾	15		17		25		ns	
PORT-TO-POF	RT DELAY TIMING								
twdd	Write Pulse to Data Delay ⁽¹⁾		45		50		60	ns	
todd	Write Data Valid to Read Data Delay ⁽¹⁾		30		35		45	ns	
NOTES:	·	•	-	-		5	-	3190 tbl 14b	

1. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveformof Write with Port-to-Port Read and BUSY (M/S = VIH)".

2. To ensure that the earlier of the two ports wins.

3. tBDD is a calculated parameter and is the greater of 0, twDD - twP (actual) or tDDD - tDW (actual).

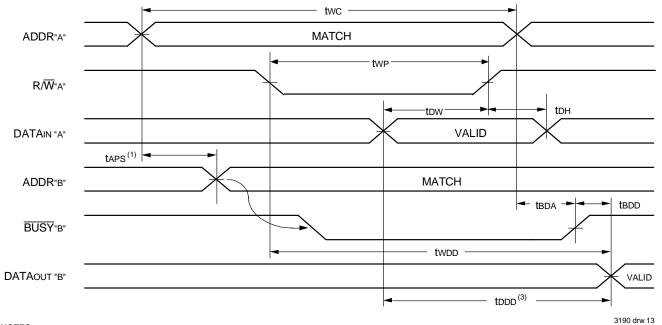
4. To ensure that the write cycle is inhibited on Port "B" during contention on Port "A".

5. To ensure that a write cycle is completed on Port "B" after contention on Port "A".

6. 'X' in part numbers indicates power rating (S or L).

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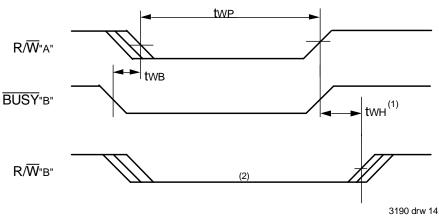
Timing Waveform of Read with $\overline{BUSY}^{(2,4,5)}(M/\overline{S} = VIH)$



NOTES:

- 1. To ensure that the earlier of the two ports wins. tAPS is ignored for $M/\overline{S}{=}V{\shortparallel}L$
- 2. $\overline{CE}L = \overline{CE}R = VIL.$
- 3. $\overline{OE} = V_{IL}$ for the reading port.
- 4. If M/S=VIL (SLAVE), BUSY is an input. Then for this example BUSY A" = VIH and BUSY B" input is shown above.
- 5. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from Port "A".

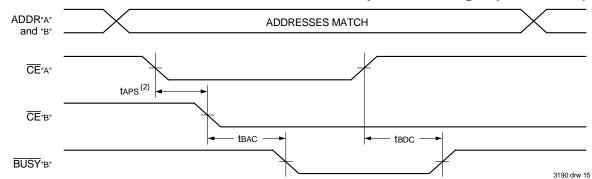
Timing Waveform of Write with **BUSY**⁽³⁾



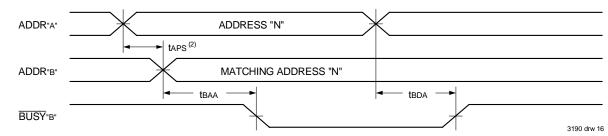
- 1. twH must be met for both BUSY input (SLAVE) and output (MASTER).
- 2. BUSY is asserted on port "B" blocking R/W"B", until BUSY"B" goes HIGH.
- 3. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from Port "A".

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Waveform of **BUSY** Arbitration Controlled by \overline{CE} Timing⁽¹⁾ (M/ \overline{S} = VIH)



Waveform of **BUSY** Arbitration Cycle Controlled by Address Match Timing⁽¹⁾ (M/S = VIH)



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from "A".

2. If tAPS is not satisfied, the BUSY signal will be asserted on one side or another but there is no guarantee on which side BUSY will be asserted.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽¹⁾

			6X12 I Only	7016X15 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
INTERRUPT T	MING					
tas	Address Set-up Time	0		0		ns
twn	Write Recovery Time	0		0		ns
tins	Interrupt Set Time		12		15	ns
tinr	Interrupt Reset Time		12		15	ns

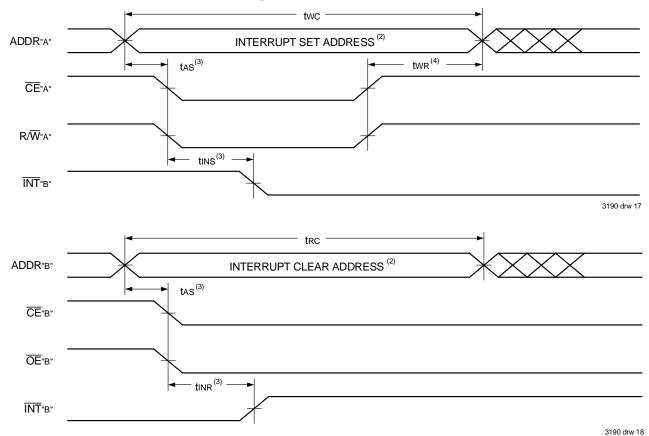
		7016X20 Com'l, Ind & Military		7016X25 Com'l & Military		7016X35 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
INTERRUPT T	IMING							
tas	Address Set-up Time	0		0		0	_	ns
twR	Write Recovery Time	0		0		0	_	ns
tins	Interrupt Set Time		20	_	20		25	ns
tinr	Interrupt Reset Time		20		20		25	ns

NOTES:

1. 'X' in part numbers indicates power rating (S or L).

3190 thi 15a

Waveform of Interrupt Timing⁽¹⁾



NOTES:

- 1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from "A".
- 2. See Interrupt truth table.
- 3. Timing depends on which enable signal (\overline{CE} or R/\overline{W}) is asserted last. 4. Timing depends on which enable signal (\overline{CE} or R/\overline{W}) is de-asserted first.

Truth Table III — Interrupt Flag⁽¹⁾

	Left Port					Right Port				
R/₩L	CEL	ŌĒL	A13L-A0L	ĨNT∟	R/WR	CER	ŌĒR	A13R-A0R	ĪNTR	Function
L	L	Х	3FFF	Х	Х	Х	Х	Х	L ⁽²⁾	Set Right INTR Flag
Х	Х	х	Х	Х	Х	L	L	3FFF	H ⁽³⁾	Reset Right INTR Flag
Х	Х	Х	Х	L ⁽³⁾	L	L	Х	3FFE	Х	Set Left ĪNT∟ Flag
Х	L	L	3FFE	H ⁽²⁾	Х	Х	Х	Х	Х	Reset Left INTL Flag

NOTES:

1. Assumes $\overline{\text{BUSY}}_{L} = \overline{\text{BUSY}}_{R} = \text{ViH}.$

2. If $\overline{\text{BUSY}}_{L} = V_{IL}$, then no change.

3. If $\overline{\text{BUSY}}_{R} = \text{VIL}$, then no change.

3190 tbl 16

Truth Table IV — Address **BUSY** Arbitration

	In	puts	Out	puts	
CEL	ĊĒr	Aol-A13L Aor-A13r	BUSYL ⁽¹⁾	BUSYR ⁽¹⁾	Function
Х	Х	NO MATCH	н	н	Normal
Н	Х	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

NOTES:

3190 tbl 17

1. Pins BUSYL and BUSYR are both outputs when the part is configured as a master. Both are inputs when configured as a slave. BUSYx outputs on the IDT7016 are push-pull, not open drain outputs. On slaves the BUSYx input internally inhibits writes.

 "L" if the inputs to the opposite port were stable prior to the address and enable inputs of this port. "H" if the inputs to the opposite port became stable after the address and enable inputs of this port. If tAPS is not met, either BUSYL or BUSYR = LOW will result. BUSYL and BUSYR outputs can not be LOW simultaneously.

Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

Truth Table V — Example of Semaphore Procurement Sequence^(1,2,3)

Functions	Do - Do Left	Do - Da Right	Status
No Action	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Right Port Writes "0" to Semaphore	0	1	No change. Right side has no write access to semaphore
Left Port Writes "1" to Semaphore	1	0	Right port obtains semaphore token
Left Port Writes "0" to Semaphore	1	0	No change. Left port has no write access to semaphore
Right Port Writes "1" to Semaphore	0	1	Left port obtains semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free
Right Port Writes "0" to Semaphore	1	0	Right port has semaphore token
Right Port Writes "1" to Semaphore	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free

3190 tbl 18

NOTES:

1. This table denotes a sequence of events for only one of the eight semaphores on the IDT7016.

2. There are eight semaphore flags written to via I/Oo and read from all I/Os (I/Oo - I/Os). These eight semaphores are addressed by Ao - A2.

e. $\overline{CE} = V_{IH}$, $\overline{SEM} = V_{IL}$ to access the semaphores. Refer to the semaphore Read/Write Truth Table.

Functional Description

The IDT7016 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT7016 has an automatic power down feature controlled by \overline{CE} . The \overline{CE} controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected (\overline{CE} HIGH). When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag (INTL) is asserted when the right port writes to memory location 3FFE

where a write is defined as the $\overline{CE} = R/\overline{W} = V_{IL}$ per Truth Table III. The left port clears the interrupt by an address location 3FFE access when $\overline{CE}_R = \overline{OE}_R = V_{IL}$, R/\overline{W} is a "don't care". Likewise, the right port interrupt flag (INTR) is asserted when the left port writes to memory location 3FFF and to clear the interrupt flag (INTR), the right port must access memory location 3FFF. The message (9 bits) at 3FFE or 3FFF is user-defined since it is in an addressable SRAM location. If the interrupt function is not used, address locations 3FFE and 3FFF are not used as mail boxes but are still part of the random access memory. Refer to Truth Table III for the interrupt operation.

Busy Logic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "busy". The $\overline{\text{BUSY}}$ pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a $\overline{\text{BUSY}}$ indication, the write signal is gated internally to prevent the write from proceeding.

The use of \overline{BUSY} logic is not required or desirable for all applications. In some cases it may be useful to logically OR the \overline{BUSY} outputs together and use any \overline{BUSY} indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of \overline{BUSY} logic is not desirable, the \overline{BUSY} logic can be disabled by placing the part in slave mode with the M/\overline{S} pin. Once in slave mode the \overline{BUSY} pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the \overline{BUSY} pins HIGH. If desired, unintended write operations can be prevented to a port by tying the \overline{BUSY} pin for that port LOW.

The BUSY outputs on the IDT7016 RAM in master mode, are pushpull type outputs and do not require pull up resistors to operate. If these RAMs are being expanded in depth, then the BUSY indication for the resulting array requires the use of an external AND gate.

Width Expansion Busy Logic Master/Slave Arrays

When expanding an IDT7016 RAM array in width while using \overline{BUSY} logic, one master part is used to decide which side of the RAM array will receive a \overline{BUSY} indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master use the \overline{BUSY} signal as a write inhibit signal. Thus on the IDT7016 RAM the \overline{BUSY} pin is an output if the part is used as a master (M/ \overline{S} pin = H), and the \overline{BUSY} pin is an input if the part used as a slave (M/ \overline{S} pin = L) as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating BUSY on one side of the array and another master indicating BUSY on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The BUSY arbitration, on a master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a \overline{BUSY} flag to be output from the master before the actual write pulse can be initiated with the R/W signal. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

Semaphores

The IDT7016 are extremely fast Dual-Port 16Kx9 Static RAMs with an additional 8 address locations dedicated to binary semaphore flags. These flags allow either processor on the left or right side of the Dual-Port RAM to claim a privilege over the other processor for functions defined by the system designer's software. As an example, the semaphore can be used by one processor to inhibit the other from accessing a portion of the Dual-Port RAM or any other shared resource.

The Dual-Port RAM features a fast access time, and both ports are completely independent of each other. This means that the activity on the

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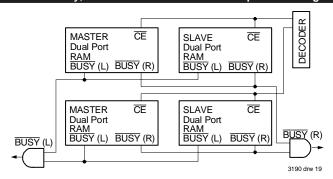


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT7016 RAMs.

left port in no way slows the access time of the right port. Both ports are identical in function to standard CMOS Static RAM and can be read from, or written to, at the same time with the only possible conflict arising from the simultaneous writing of, or a simultaneous READ/WRITE of, a non-semaphore location. Semaphores are protected against such ambiguous situations and may be used by the system program to avoid any conflicts in the non-semaphore portion of the Dual-Port RAM. These devices have an automatic power-down feature controlled by \overline{CE} , the Dual-Port RAM enable, and \overline{SEM} , the semaphore enable. The \overline{CE} and \overline{SEM} pins control on-chip power down circuitry that permits the respective port to go into standby mode when not selected. This is the condition which is shown in Truth Table I where \overline{CE} and \overline{SEM} are both HIGH.

Systems which can best use the IDT7016 contain multiple processors or controllers and are typically very high-speed systems which are software controlled or software intensive. These systems can benefit from a performance increase offered by the IDT7016's hardware semaphores, which provide a lockout mechanism without requiring complex programming.

Software handshaking between processors offers the maximum in system flexibility by permitting shared resources to be allocated in varying configurations. The IDT7016 does not use its semaphore flags to control any resources through hardware, thus allowing the system designer total flexibility in system architecture.

An advantage of using semaphores rather than the more common methods of hardware arbitration is that wait states are never incurred in either processor. This can prove to be a major advantage in very highspeed systems.

How the Semaphore Flags Work

The semaphore logic is a set of eight latches which are independent of the Dual-Port RAM. These latches can be used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphores provide a hardware assist for a use assignment method called "Token Passing Allocation." In this method, the state of a semaphore latch is used as a token indicating that shared resource is in use. If the left processor wants to use this resource, it requests the token by setting the latch. This processor then verifies its success in setting the latch by reading it. If it was successful, it proceeds to assume control over the shared resource. If it was not successful in setting the latch, it determines that the right side processor has set the latch first, has the token and is using the shared resource. The left processor can then either repeatedly request that semaphore's status or remove its request for that semaphore to

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perform another task and occasionally attempt again to gain control of the token via the set and test sequence. Once the right side has relinquished the token, the left side should succeed in gaining control.

The semaphore flags are active LOW. A token is requested by writing a zero into a semaphore latch and is released when the same side writes a one to that latch.

The eight semaphore flags reside within the IDT7016 in a separate memory space from the Dual-Port RAM. This address space is accessed by placing a LOW input on the \overline{SEM} pin (which acts as a chip select for the semaphore flags) and using the other control pins (Address, \overline{OE} , and R/\overline{W}) as they would be used in accessing a standard static RAM. Each of the flags has a unique address which can be accessed by either side through address pins A0–A2. When accessing the semaphores, none of the other address pins has any effect.

When writing to a semaphore, only data pin Do is used. If a low level is written into an unused semaphore location, that flag will be set to a zero on that side and a one on the other side (see Truth Table V). That semaphore can now only be modified by the side showing the zero. When a one is written into the same location from the same side, the flag will be set to a one for both sides (unless a semaphore request from the other side is pending) and then can be written to by both sides. The fact that the side which is able to write a zero into a semaphore subsequently locks out writes from the other side is what makes semaphore flags useful in interprocessor communications. (A thorough discussion on the use of this feature follows shortly.) A zero written into the same location from that side until the semaphore is freed by the first side.

When a semaphore flag is read, its value is spread into all data bits so that a flag that is a one reads as a one in all data bits and a flag containing a zero reads as all zeros. The read value is latched into one side's output register when that side's semaphore select (SEM) and output enable (\overline{OE}) signals go active. This serves to disallow the semaphore from changing state in the middle of a read cycle due to a write cycle from the other side. Because of this latch, a repeated read of a semaphore in a test loop must cause either signal (SEM or \overline{OE}) to go inactive or the output will never change.

A sequence WRITE/READ must be used by the semaphore in order to guarantee that no system level contention will occur. A processor requests access to shared resources by attempting to write a zero into a semaphore location. If the semaphore is already in use, the semaphore request latch will contain a zero, yet the semaphore flag will appear as one, a fact which the processor will verify by the subsequent read (see Truth Table V). As an example, assume a processor writes a zero to the left port at a free semaphore location. On a subsequent read, the processor will verify that it has written successfully to that location and will assume control over the resource in question. Meanwhile, if a processor on the right side attempts to write a zero to the same semaphore flag it will fail, as will be verified by the fact that a one will be read from that semaphore on the right side during subsequent read. Had a sequence of READ/WRITE been used instead, system contention problems could have occurred during the gap between the read and write cycles.

It is important to note that a failed semaphore request must be followed by either repeated reads or by writing a one into the same location. The reason for this is easily understood by looking at the simple logic diagram of the semaphore flag in Figure 4. Two semaphore request latches feed into a semaphore flag. Whichever latch is first to present a zero to the semaphore flag will force its side of the semaphore flag LOW and the other side HIGH. This condition will continue until a one is written to the same semaphore request latch. Should the other side's semaphore request latch have been written to a zero in the meantime, the semaphore flag will flip over to the other side as soon as a one is written into the first side's request latch. The second side's flag will now stay LOW until its semaphore request latch is written to a one. From this it is easy to understand that, if a semaphore is requested and the processor which requested it no longer needs the resource, the entire system can hang up until a one is written into that semaphore request latch.

The critical case of semaphore timing is when both sides request a single token by attempting to write a zero into it at the same time. The semaphore logic is specially designed to resolve this problem. If simultaneous requests are made, the logic guarantees that only one side receives the token. If one side is earlier than the other in making the request, the first side to make the request will receive the token. If both requests arrive at the same time, the assignment will be arbitrarily made to one port or the other.

One caution that should be noted when using semaphores is that semaphores alone do not guarantee that access to a resource is secure. As with any powerful programming technique, if semaphores are misused or misinterpreted, a software error can easily happen.

Initialization of the semaphores is not automatic and must be handled via the initialization program at power-up. Since any semaphore request flag which contains a zero must be reset to a one, all semaphores on both sides should have a one written into them at initialization from both sides to assure that they will be free when needed.

Using Semaphores—Some Examples

Perhaps the simplest application of semaphores is their application as resource markers for the IDT7016's Dual-Port RAM. Say the 16K x 9 RAM was to be divided into two 8K x 9 blocks which were to be dedicated at any one time to servicing either the left or right port. Semaphore 0 could be used to indicate the side which would control the lower section of memory, and Semaphore 1 could be defined as the indicator for the upper section of memory.

To take a resource, in this example the lower 8K of Dual-Port RAM, the processor on the left port could write and then read a zero in to Semaphore 0. If this task were successfully completed (a zero was read back rather than a one), the left processor would assume control of the lower 8K. Meanwhile the right processor was attempting to gain control of the resource after the left processor, it would read back a one in response to the zero it had attempted to write into Semaphore 0. At this point, the software could choose to try and gain control of the second 8K section by writing, then reading a zero into Semaphore 1. If it succeeded in gaining control, it would lock out the left side.

Once the left side was finished with its task, it would write a one to Semaphore 0 and may then try to gain access to Semaphore 1. If Semaphore 1 was still occupied by the right side, the left side could undo its semaphore request and perform other tasks until it was able to write, then read a zero into Semaphore 1. If the right processor performs a similar task with Semaphore 0, this protocol would allow the two processors to swap 8K blocks of Dual-Port RAM with each other.

The blocks do not have to be any particular size and can even be variable, depending upon the complexity of the software using the

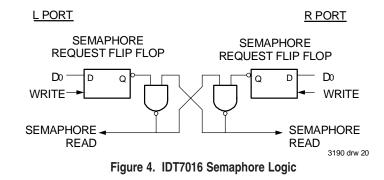
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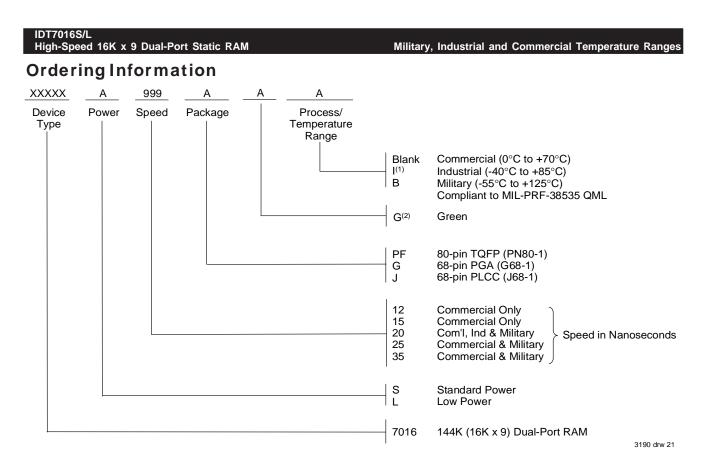
semaphore flags. All eight semaphores could be used to divide the Dual-Port RAM or other shared resources into eight parts. Semaphores can even be assigned different meanings on different sides rather than being given a common meaning as was shown in the example above.

Semaphores are a useful form of arbitration in systems like disk interfaces where the CPU must be locked out of a section of memory during a transfer and the I/O device cannot tolerate any wait states. With the use of semaphores, once the two devices has determined which memory area was "off-limits" to the CPU, both the CPU and the I/O devices could access their assigned portions of memory continuously without any wait states.

Semaphores are also useful in applications where no memory "WAIT" state is available on one or both sides. Once a semaphore handshake has been performed, both processors can access their assigned RAM segments at full speed.

Another application is in the area of complex data structures. In this case, block arbitration is very important. For this application one processor may be responsible for building and updating a data structure. The other processor then reads and interprets that data structure. If the interpreting processor reads an incomplete data structure, a major error condition may exist. Therefore, some sort of arbitration must be used between the two different processors. The building processor arbitrates for the block, locks it and then is able to go in and update the data structure. When the update is completed, the data structure block is released. This allows the interpreting processor to come back and read the complete data structure, thereby guaranteeing a consistent data structure.





NOTES:

- 1. Contact your local sales office for industrial temp range for other speeds, packages and powers.
- 2. Green parts available. For specific speeds, packages and powers contact your local sales office.

Datasheet Document History

01/11/99:		Initiated datasheet document history
		Converted to new format
		Cosmetic and typographical corrections
	Pages 2 and 3	Added additional notes to pin configurations
06/03/99		Changed drawing format
	Page 1	Corrected DSC number
11/10/99:		Replaced IDT logo
05/19/00:	Page 4	Increased storage temperature parameter
		Clarified TA parameter
	Page 6	DC Electrical parameters-changed wording from open to disabled
		Changed ±200mV to 0mV in notes
01/10/02:	Pages 2 & 3	Added date revision for pin configurations
	Pages 4, 6, 7, 9 & 12	Removed Industrial temp footnote from all tables
	Pages 6, 7, 9, 12 & 14	Added Industrial temp for 20ns speed to DC and AC Electrical Characteristics
	Page 20	Added Industrial temp offering to 20ns ordering information
	Pages 1 & 20	Replaced ™ logo with ® logo
04/04/06:	Page 1	Added green availability to features
	Page 20	Added indicator to ordering information
01/09/09:	Page 20	Removed "IDT" from orderable part number

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